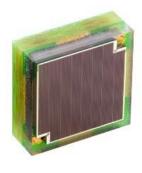


Product Data Sheet SiPM – Silicon Photomultiplier PM3325-EB / PM3350-EB





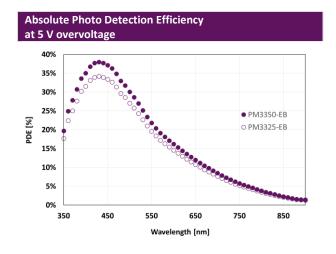


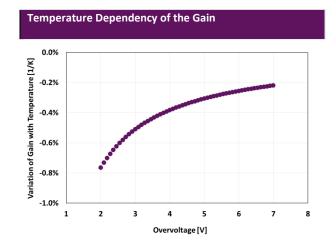
PM33 Series in new Chip Size Package

Key Features Overview

- High Photo Detection Efficiency
- Excellent Timing Properties
- Extremely low Temperature Coefficient
- New Chip Size Package suitable for Arrays
- MSL1 approved

1. SiPM Key Features





2. SiPM General Parameters

General Para	meters				
Туре	Active Area [mm²]	Microcell Size [μm]	No. of Microcells	Package Dimensions [mm³]	Order-Code
PM33	3.0 x 3.0	25	13408	3.50 x 3.50 x 1.45	PM3325-EB
FIVIOO	3.0 X 3.0	50	3472	5.50 x 5.50 x 1.45	PM3350-EB

3. Main Characteristics

Main Characteristics		
Parameter	Тур.	Unit
Breakdown Voltage (V _{BD})	25.0	V
Recommended Overvoltage (Vov)	2.0 – 7.0	V
Temperature Dependency of V _{BD}	18.0	mV/K
Temperature Dependency of Gain	0.3% @ 5.0 Vov	1/K









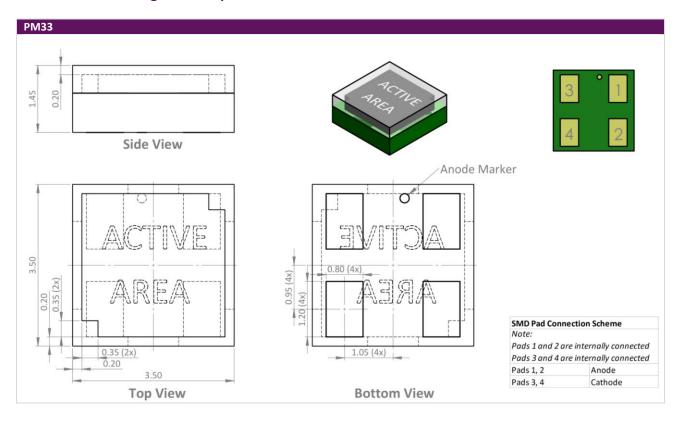
Product Data Sheet SiPM – Silicon Photomultiplier PM3325-EB / PM3350-EB



4. Performance Overview

Parameter	Туре	Microcell Size [μm]	Typ. @ 2.5 V _{ov}	Typ. @ 5.0 V _{ov}	Unit
Photo Detection	DMA22	25	26	34	%
Efficiency @ 430 nm	PM33	50	28	38	
Dark Count Rate	PM33	25	250	500	kHz/mm²
		50	250	500	
Crosstall, Drobability	PM33	25	10	30	%
Crosstalk Probability		50	10	25	
Afterpulse Probability	PM33	25	1	3	%
		50			
Cain	PM33	25	0.9	1.7	x 10 ⁶
Gain		50	3.6	7.2	
Terminal Capacitance	PM33	25	790		pF
		50	810		
Recovery Time τ	PM33	25	35		ns
		50	130		
Signal Rise Time	PM33	25	<1		
		50	< 1		ns

5. Technical Drawing and Footprint







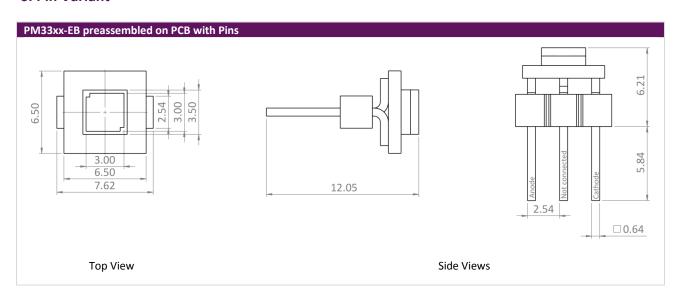




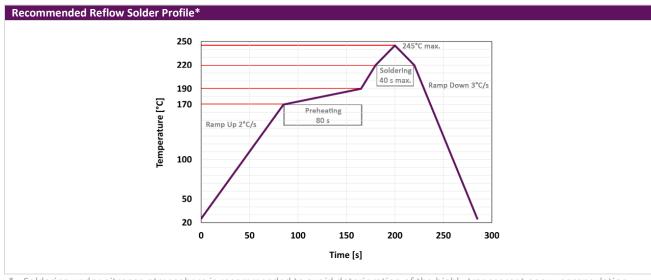
Product Data Sheet SiPM – Silicon Photomultiplier PM3325-EB / PM3350-EB



6. Pin Variant



7. Reflow Solder Profile



^{*} Soldering under nitrogen atmosphere is recommended to avoid deterioration of the highly transparent epoxy encapsulation





